

ABSTRACT

A thin film capacitance element composition,
5 wherein a bismuth layer compound having a c-axis oriented vertically with respect to a substrate surface is expressed by a composition formula of $(Bi_2O_2)^{2+} (A_{m-1} B_m O_{3m+1})^{2-}$ or $Bi_2A_{m-1} B_m O_{3m+3}$, wherein "m" is an even number, "A" is at least one element selected from Na, K, Pb, Ba,
10 Sr, Ca and Bi, and "B" is at least one element selected from Fe, Co, Cr, Ga, Ti, Nb, Ta, Sb, V, Mo and W; and Bi in the bismuth layer compound is excessively included with respect to the composition formula of $(Bi_2O_2)^{2+} (A_{m-1} B_m O_{3m+1})^{2-}$ or $Bi_2A_{m-1} B_m O_{3m+3}$, and the excessive content of
15 Bi is in a range of $0 < Bi < 0.5 \times m$ mol in terms of Bi.